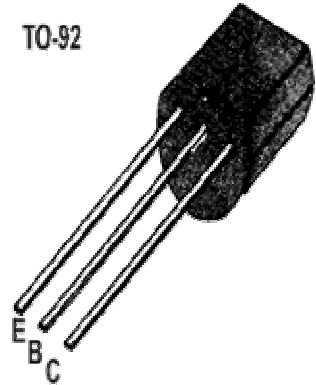


**■ ■ APPLICATION:** General Purpose Applications.

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	$V_{CBO}$	-80	V
Collector-emitter voltage	$V_{CEO}$	-60	V
Emitter-base voltage	$V_{EBO}$	-8	V
Collector current	$I_C$	-700	mA
Collector Power Dissipation	$P_C$	800	mW
Junction Temperature	$T_J$	150	°C
Storage Temperature Range	$T_{stg}$	- 55~150	°C


**■ ■ ELECTRICAL CHARACTERISTICS** ( $T_a=25$ )

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	$h_{FE}$	40		240		$V_{CE} = -2V, I_C = -50mA$
Collector Cut-off Current	$I_{CBO}$			-0.1	$\mu A$	$V_{CB} = -60V, I_E = 0$
Emitter Cut-off Current	$I_{EBO}$			-0.1	$\mu A$	$V_{EB} = -5V, I_C = 0$
Collector-Base Breakdown Voltage	$BV_{CBO}$	-80			V	$I_C = -0.1mA, I_E = 0$
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	-60			V	$I_C = -10mA, I_B = 0$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-8			V	$I_E = -0.1mA, I_C = 0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.3	-0.7	V	$I_C = -500mA, I_B = -50mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.9	-1.1	V	$I_C = -500mA, I_B = -50mA$
Gain bandwidth product	$f_T$		50		MHz	$I_C = -50mA, V_{CE} = -10V$
Common Base Output Capacitance	$C_{ob}$		13		PF	$V_{CB} = -10V, I_E = 0, f = 1MHz$

**■ ■  $h_{FE}$  Classification**

Classification	R	O	Y
$h_{FE}$	40~80	70~140	120~240